L	Hits	Search Text	DB	Time stamp
Number				
1	273	(gate with germanium) same \$4silicon same nitride	USPAT; US-PGPUB; EPO; JPO;	2004/03/03 17:43
2	87	((gate with germanium) same \$4silicon same nitride) and (@ad<19990623 or @rlad<19990623)	DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/03 17:43
3	3	((polysilicon with over with germanium with gate) same nitride) and (@ad<19990623)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/03 17:41
4	2	((polysilicon with top with germanium with gate) same nitride) and (@ad<19990623)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/03 17:41
5	76	(((gate with germanium) same \$4silicon same nitride) and (@ad<19990623 or @rlad<19990623)) and dop\$3	USPAT; US-PGPUB; EPO; JPO;	2004/03/03 17:43
6	99	(gate with germanium) same \$4silicon same nitride same dop\$3	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/03/03 17:43
7	32	((gate with germanium) same \$4silicon same nitride same dop\$3) and (@ad<19990623 or @rlad<19990623)	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/03/03 17:43
-	212	(gate adj1 electrode) with germanium	DERWENT USPAT; EPO; JPO; DERWENT	2004/03/03 16:16
-	2	((gate adj1 electrode) with germanium) same (conduct\$3 adj1 film)	USPAT; EPO; JPO; DERWENT	2002/01/23 10:26
-	13	((gate adj1 electrode) with germanium) and (conduct\$3 adj1 film)	USPAT; EPO; JPO; DERWENT	2002/01/23 10:26
-	9	((gate adj1 electrode) with germanium) same (p-type near3 dop\$3)	USPAT; EPO; JPO; DERWENT	2002/01/23 16:26
-	2	((gate adjl electrode) with germanium) same (silicon adjl substrate) same MOSFET	USPAT; EPO; JPO; DERWENT	2002/01/24 08:55
-	31	((gate adj1 electrode) with germanium) and (silicon adj1 substrate) and MOSFET	USPAT; EPO; JPO; DERWENT	2002/01/24 10:23
-	11	"5216271"	USPAT; EPO; JPO; DERWENT	2002/01/31 13:12
_	8	"5101247"	USPAT; EPO; JPO; DERWENT	2002/01/31 13:49
-	2511	conduct\$3 with (transition near3 metal)	USPAT; JPO; DERWENT	2002/01/31 15:42
-	0	(conduct\$3 with (transition near3 metal)) and (gate near4 germanium)	USPAT; JPO; DERWENT	2002/01/31 15:38
-	. 9	(conduct\$3 with (transition near3 metal)) and gate and germanium	USPAT; JPO; DERWENT	2002/01/31 15:24
-	0	(conduct\$3 with (transition near3 metal)) same (gate and germanium)	USPAT; JPO; DERWENT	2002/01/31 15:40
-	104	(conduct\$3 with (transition near3 metal)) and (metal near2 silicide)	USPAT; JPO; DERWENT	2002/01/31 15:40
_	407	(conduct\$3 near3 (film or layer)) with (transition near3 metal)	USPAT; JPO; DERWENT	2002/01/31 15:59

Search History 3/3/04 5:47:16 PM Page 1

		<u></u>		
_	931	(germanium near2 (film or layer)) and	USPAT;	2002/02/01
		(conduct\$3 near2 (film or layer))	JPO;	10:33
		(0011440040 110412 (111111 01 14)01//	DERWENT	
	25.600	(2002/02/01
-	35609	(polysilicon near2 (layer or film))	USPAT;	
			JPO;	10:27
			DERWENT	
_	150	((polysilicon near2 (layer or film))) and	USPAT;	2002/02/01
		((germanium near2 (film or layer)) and	JPO;	10:31
				10.31
		(conduct\$3 near2 (film or layer)))	DERWENT	
-	0	"polysilicon layer between a germanium	USPAT;	2002/02/01
		layer and a conducitive layer"	JPO;	10:33
		1	DERWENT	
	150	/	USPAT;	2002/02/01
_	158	(germanium near2 (film or layer)) with	· ·	
		(conduct\$3 near2 (film or layer))	JPO;	11:18
			DERWENT	
_	11	((germanium near2 (film or layer)) with	USPAT;	2002/02/01
		(conduct\$3 near2 (film or layer))) with	JPO;	10:36
			DERWENT	10.50
		(polysilicon near2 (layer or film))		0000/00/01
-	6		USPAT;	2002/02/01
1		(conduct\$3 near2 (film or layer))) with	JPO;	11:00
		silicide	DERWENT	
	1676		USPAT;	2002/02/01
-	1676			,
	İ	(\$4silicon near2 (film or layer))	JPO;	11:23
			DERWENT	1
<u>-</u>	35	((germanium near2 (film or layer)) with	USPAT;	2002/02/01
		(\$4silicon near2 (film or layer))) with	JPO;	11:23
			DERWENT	
1		silicide		2002/02/01
-	12	"5608249"	USPAT;	2002/02/01
1			JPO;	14:09
1			DERWENT	l l
1_	83	(gate adj (dielectric or insulator)) with	USPAT;	2002/09/15
1 -	0.3		EPO; JPO;	19:03
1		(germanium or ge)		1 2 3 . 0 3
1			DERWENT	
-	67	((gate adj (dielectric or insulator))	USPAT;	2002/09/15
1	1	with (germanium or ge)) and @ad<19992306	EPO; JPO;	19:05
		(9	DERWENT	
1		//wata add /dialaatmia am imaniatami\	USPAT;	2002/09/22
I -	58			
	1	with (germanium or ge)) and @ad<19990623	EPO; JPO;	09:08
			DERWENT	i
l	18	((germanium or ge) adj (film or layer))	USPAT;	2002/09/19
	1	with (gate adj insulat\$3)	EPO; JPO;	15:59
	1	with (gate ad) imparately)	DERWENT	'
	1			1 2002 (00 (10
-	16		USPAT;	2002/09/19
	1	with (gate adj insulat\$3)) and	EPO; JPO;	16:00
1	1	@ad<19990623	DERWENT	
1_	10	(((gate adj electrode) with (germanium or	USPAT;	2002/09/22
_	"	(//gate ad) cicotions/ with /germanium or	EPO; JPO;	09:11
1	1	ge)) and @ad<19990623) and ((gate adj		09.11
1	1	(insulator or dielectric)) with	DERWENT	
	1	(germanium or ge))	}	
-	382		USPAT;	2002/09/22
	332	ge)) and @ad<19990623	EPO; JPO;	09:27
	1	90// and Gaa(15550025	DERWENT	
		11. 5 . 129 . 3 . 1 . 2 . 2 . 2 . 2 . 2 . 2 . 2 . 2 . 2	1	2002/04/11
-	157		USPAT;	2003/04/11
	1	ge)) same (gate adj (dielectric or	US-PGPUB;	14:01
	1	insulat\$3 or \$20xide)) and (dop\$3 same	EPO; JPO;	
	1	("p-type" or boron or b or al or aluminum	DERWENT	
	1			
		or ga or in))	HODAE	2002/04/11
-	44	1 1112 1 1	USPAT;	2003/04/11
		or ge)) same (gate adj (dielectric or	US-PGPUB;	15:30
		insulat\$3 or \$20xide)) and (dop\$3 same	EPO; JPO;	
		("p-type" or boron or b or al or aluminum	DERWENT	
	1			
	_	or ga or in))) and @ad<19990623	,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	1 2002 /04 /23
-	0	(germanium near3 gate) same	USPAT;	2003/04/11
		"1.times.10.sup.\$2"	US-PGPUB;	15:21
		_	EPO; JPO;	
			DERWENT	1
	_	/gommanium noana gatal gama		2003/04/11
-	3		USPAT;	
		("1.times.10.sup.17" or	US-PGPUB;	15:25
	1	"1.times.10.sup.18" or	EPO; JPO;	
	1	"1.times.10.sup.19" or	DERWENT	
		"1.times.10.sup.20")	···	ļ 1
L	1	1. CIMCS. 10. Sup. 20 /	1	ı

-	3	(germanium with gate with electrode) same	USPAT;	2003/04/11
		("1.times.10.sup.17" or	US-PGPUB;	16:00
		"1.times.10.sup.18" or	EPO; JPO;	
		"1.times.10.sup.19" or	DERWENT	
		"1.times.10.sup.20")		0000/04/11
-	20	(germanium with film) same "p-type" same	USPAT;	2003/04/11
		impurities same dop\$3	US-PGPUB;	15:29
			EPO; JPO;	
			DERWENT	0000/04/11
-	15	((germanium with film) same "p-type" same	USPAT;	2003/04/11
		impurities same dop\$3) and @ad<19990623	US-PGPUB;	16:00
			EPO; JPO;	
		611-1	DERWENT	2002/04/11
_	44	(germanium with film) same	USPAT; US-PGPUB;	2003/04/11
		("1.times.10.sup.17" or	EPO; JPO;	116:13
		"1.times.10.sup.18" or	DERWENT	
		"1.times.10.sup.19" or	DERMENT	
	19	((germanium with film) same	USPAT;	2003/04/11
_	19	("1.times.10.sup.17" or	US-PGPUB;	16:12
			EPO; JPO;	10.12
1		"1.times.10.sup.18" or	DERWENT	
		"1.times.10.sup.19" of	DELMARIAT	
_	701	(ge or germanium) with "above" with oxide	USPAT;	2003/04/11
-	/01	(ge of germanium) with above with oxide	US-PGPUB;	16:12
			EPO; JPO;	* " . * 2
	İ		DERWENT	
_	519	((ge or germanium) with "above" with	USPAT;	2003/04/11
-	1 313	oxide) and @ad<19990623	US-PGPUB;	17:00
ļ		Oxide/ and edd(19990023	EPO; JPO;	
	1		DERWENT	
_	7	(((ge or germanium) with "above" with	USPAT;	2003/04/11
	'	oxide) and @ad<19990623) and	US-PGPUB;	17:08
	j	("1.times.10.sup.17" or	EPO; JPO;	
		"1.times.10.sup.18" or	DERWENT	1
		"1.times.10.sup.19" or		1 1
		"1.times.10.sup.20")		
_	13	(((ge or germanium) with "above" with	USPAT;	2003/04/11
į		oxide) and @ad<19990623) and (gate adj	US-PGPUB;	16:58
		(dielectric or oxide or insulat\$3)) and	EPO; JPO;	
		(gate adj electrode) and "p-type"	DERWENT	
-	l о	(germanium adj gate adj electrode) with	USPAT;	2003/04/11
		"on" with (insulat\$3 or oxide)	US-PGPUB;	17:00
1			EPO; JPO;	
			DERWENT	
-	27	germanium adj gate adj electrode	USPAT;	2003/04/11
1			US-PGPUB;	17:00
			EPO; JPO;	
1			DERWENT	
-	3	(germanium adj gate adj electrode) and	USPAT;	2003/04/11
		@ad<19990623	US-PGPUB;	17:17
			EPO; JPO;	
		l	DERWENT	0000/04/11
-	45	((ge or germanium) with electrode) same	USPAT;	2003/04/11
	ŀ	("p-type" or boron) same	US-PGPUB;	17:18
		("1.times.10.sup.17" or	EPO; JPO;	ļ
	1	"1.times.10.sup.18" or	.DERWENT	
	1	"1.times.10.sup.19" or		
		"1.times.10.sup.20")	HCD3m.	2002/04/11
-	33		USPAT;	2003/04/11
į		("p-type" or boron) same	US-PGPUB;	111.40
	[("1.times.10.sup.17" or	EPO; JPO; DERWENT	
		"1.times.10.sup.18" or	LABUMENT]
		"1.times.10.sup.19" or "1.times.10.sup.20")) and @ad<19990623		
_	3	((ge or germanium) with electrode with	USPAT;	2003/08/13
	1	((ge of germanium) with electrode with gate) same ("p-type" or boron) same	US-PGPUB;	17:31
		("1.times.10.sup.17" or	EPO; JPO;	- / · · · ·
	1	"1.times.10.sup.17" or	DERWENT	
1		"1.times.10.sup.19" or		
1		"1.times.10.sup.20")	1	
L	l	1. CIMED. 10. Dup. 20 /		

[-	5	((ge or germanium) with gate) same	USPAT;	2003/04/11
		("p-type" or boron) same	US-PGPUB;	17:34
		("1.times.10.sup.17" or "1.times.10.sup.18" or	EPO; JPO; DERWENT	
		"1.times.10.sup.19" or		
_	2	"1.times.10.sup.20") (germanium same (metal adj silicide) same	USPAT;	2003/04/11
		polysilicon same (gate adj electrode))	US-PGPUB;	17:42
		and @ad<19990623	EPO; JPO;	
_	36	 (germanium same (metal adj silicide) same	DERWENT USPAT;	2003/04/11
		polysilicon) and @ad<19990623	US-PGPUB;	18:03
			EPO; JPO; DERWENT	
_	50	(germanium with (work adj function)) same	USPAT;	2003/04/11
		(silicon with (work adj function))	US-PGPUB; EPO; JPO;	18:13
			DERWENT	
-	17	germanium with (work adj function) with	USPAT;	2003/04/11
		"ev"	US-PGPUB; EPO; JPO;	18:14
			DERWENT	0000/00/10
-	283	((gate adj1 electrode) with (germanium or ge)) same ("p-type" or b or boron or	USPAT; US-PGPUB;	2003/08/13
		aluminum or indium or gallium)	EPO; JPO;	
	41	(((gate adj1 electrode) with (germanium	DERWENT USPAT;	2003/08/13
-	41	or ge)) same ("p-type" or b or boron or	US-PGPUB;	17:50
		aluminum or indium or gallium)) and	EPO; JPO;	
		("1.times.10.sup.17" or "1.times.10.sup.18" or	DERWENT	
		"1.times.10.sup.19" or		
_	20	"1.times.10.sup.20") ((((gate adj1 electrode) with (germanium	USPAT;	2003/08/13
		or ge)) same ("p-type" or b or boron or	US-PGPUB;	18:21
		aluminum or indium or gallium)) and ("1.times.10.sup.17" or	EPO; JPO; DERWENT	
		"1.times.10.sup.17" or	DERWEINT	
		"1.times.10.sup.19" or		
_	814	(gate adj1 electrode) with (germanium or	USPAT;	2003/08/13
		ge)	US-PGPUB;	17:49
		•	EPO; JPO; DERWENT	
_	8	((gate adjl electrode) with (germanium or	USPAT;	2003/08/13
		ge)) same ("1.times.10.sup.17" or "1.times.10.sup.18" or	US-PGPUB; EPO; JPO;	17:55
		"1.times.10.sup.19" or	DERWENT	
_	2	"1.times.10.sup.20") ("5952701" "6262456"	USPAT	2003/08/13
		"2002/0113294").PN.		17:52
-	2	(work adj function) same (germanium or ge) same (mid with gap with energy with	USPAT; US-PGPUB;	2003/08/13 18:19
		silicon)	EPO; JPO;	10.17
		1111696 UDDN	DERWENT	2003/09/13
-	0	1111686.URPN.	USPAT	2003/08/13 18:05
-	5	("4984043" "4990974" "5194923"	USPAT	2003/08/13
_	39	"5250818" "5619057").PN. (boron or b) with implant\$5 with	USPAT;	18:05 2003/08/13
		(germanium or ge) with "kev"	US-PGPUB;	18:20
			EPO; JPO; DERWENT	
-	20	((boron or b) with implant\$5 with	USPAT;	2003/08/13
		(germanium or ge) with "kev") and @ad<19990623	US-PGPUB; EPO; JPO;	18:21
		eau\17770023	DERWENT	
-	31	(dop\$3 or implant\$5) with (germanium or	USPAT;	2003/08/13
		ge) with (gate adj electrode) with (boron or b)	US-PGPUB; EPO; JPO;	18:46
		<u>'</u>	DERWENT	

-	13	((dop\$3 or implant\$5) with (germanium or	USPAT;	2003/08/13
· ·		ge) with (gate adj electrode) with	US-PGPUB;	18:46
		(boron or b)) and @ad<19990623	EPO; JPO;	
			DERWENT	
-	0	jp-27854-\$.did	USPAT;	2003/08/22
			EPO; JPO;	11:24
			DERWENT	
-	0	jp-1027854-\$.did	USPAT;	2004/02/19
			EPO; JPO;	11:57
			DERWENT	
-	0	jp-027854-\$.did	USPAT;	2004/02/19
			EPO; JPO;	11:57
			DERWENT	
_	0	jp-027854-\$.did.	USPAT;	2004/02/19
			EPO; JPO;	11:58
1			DERWENT	
_	2	jp-10027854-\$.did.	USPAT;	2004/02/19
			EPO; JPO;	11:58
			DERWENT	